

ABSTRACT

An electroplating apparatus is provided with a metal target and a device for supporting a semiconductor wafer (or other workpiece) in an electroplating solution. The target (anode) may be located relatively far from the wafer surface (cathode) at the beginning of the plating process, until a sufficient amount of metal is plated. When an initial amount of metal is built up on the wafer surface, the target may be moved closer to the wafer for faster processing. The movement of the target may be controlled automatically according to one or more process parameters.